



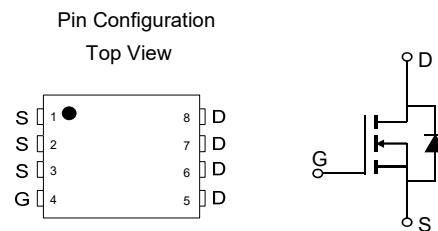
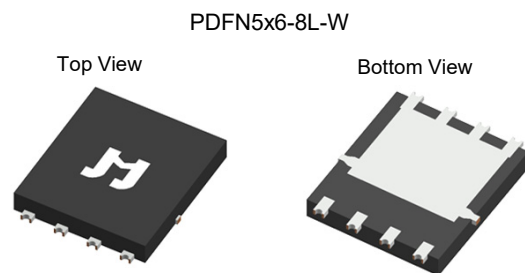
100V 2.8mΩ N-Ch Power MOSFET

Features

- Ultra-low ON-resistance, $R_{DS(ON)}$
- Low Gate Charge, Q_g
- 100% UIS and R_g Tested
- Wettable Flanks design support high manufacturability and Automated Optical Inspection (AOI)
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant
- AEC-Q101 Qualified for Automotive Applications

Product Summary

Parameter	Value	Unit
V_{DS}	100	V
$V_{GS(th)}$	2.9	V
I_D (@ $V_{GS} = 10V$) ⁽¹⁾	178	A
$R_{DS(ON)}$ (@ $V_{GS} = 10V$)	2.8	mΩ

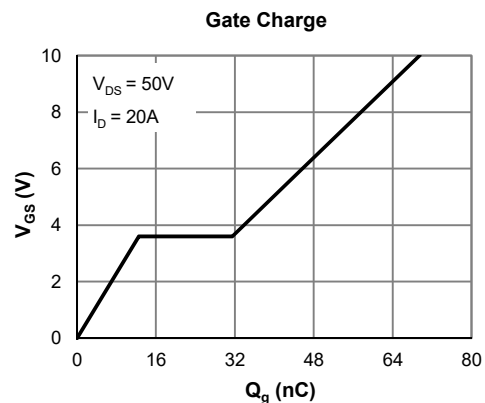
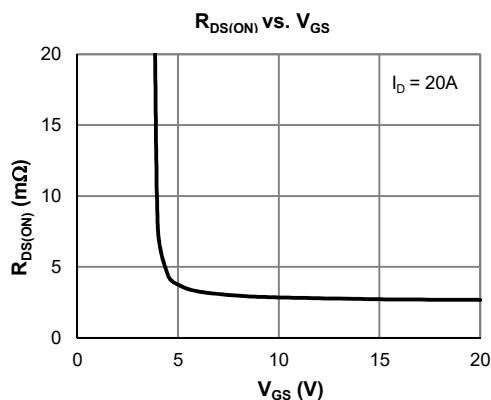


Ordering Information

Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
JMSH1003AGWQ-13	PDFN5x6-8L-W	8	SH1003AQ	1	-55 to 175	13-inch Reel	5000

Absolute Maximum Ratings (@ $T_A = 25^\circ C$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	100	V
Gate-to-Source Voltage	V_{GS}	±20	V
Continuous Drain Current ⁽¹⁾	I_D	$T_C = 25^\circ C$	178
		$T_C = 100^\circ C$	125
Pulsed Drain Current ⁽²⁾	I_{DM}	576	A
Avalanche Energy ⁽³⁾	E_{AS}	481	mJ
Power Dissipation ⁽⁴⁾	P_D	$T_C = 25^\circ C$	214
		$T_C = 100^\circ C$	107
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 175	°C





Electrical Characteristics (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80\text{V}, V_{GS} = 0\text{V}$			1.0	μA
					5.0	
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.0	2.9	4.0	V
Static Drain-Source ON-Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$		2.8	3.4	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{V}, I_D = 20\text{A}$		86		S
Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}, V_{GS} = 0\text{V}$		0.66	1.0	V
Diode Continuous Current	I_S	$T_C = 25^\circ\text{C}$			178	A

DYNAMIC PARAMETERS ⁽⁵⁾

Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 50\text{V}, f = 1\text{MHz}$		4797		pF
Output Capacitance	C_{oss}			900		pF
Reverse Transfer Capacitance	C_{rss}			19.1		pF
Gate Resistance	R_g		$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$		2.7	

SWITCHING PARAMETERS ⁽⁵⁾

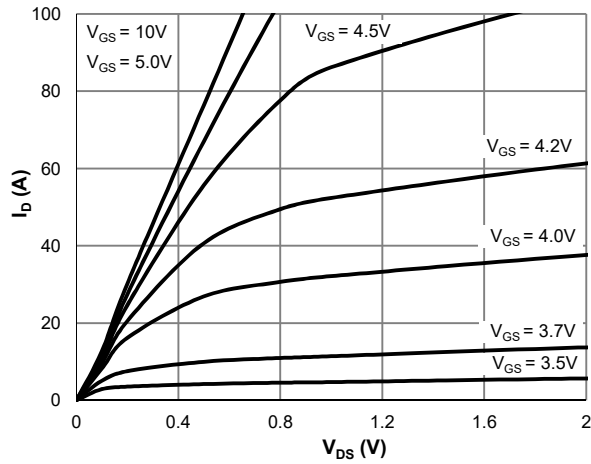
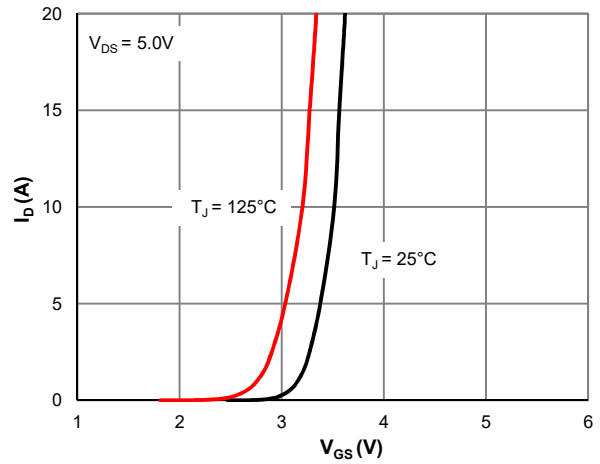
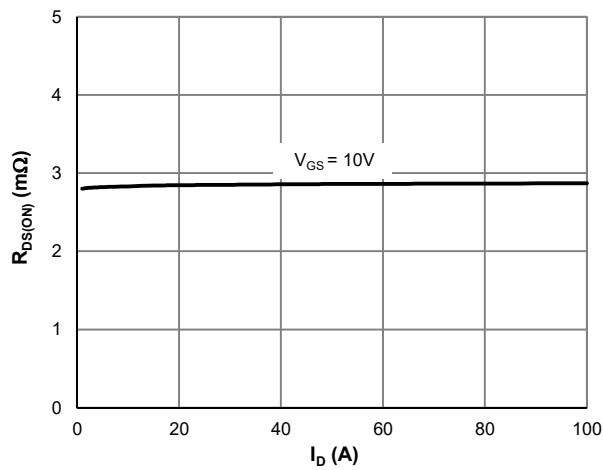
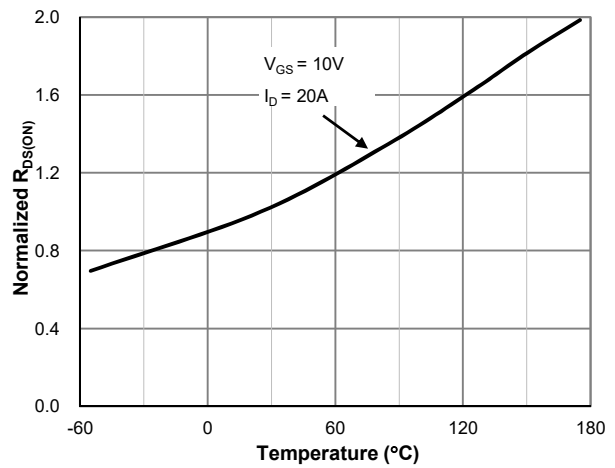
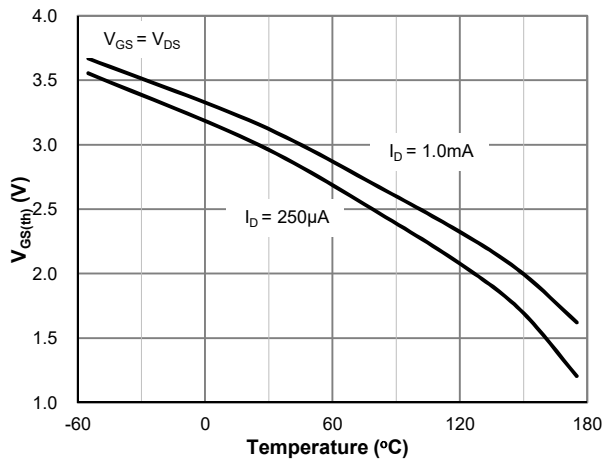
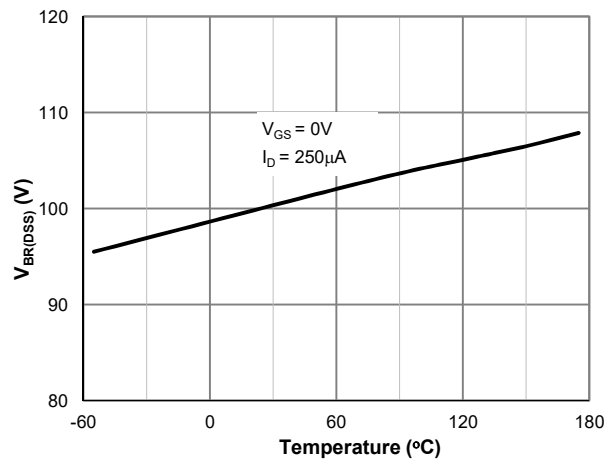
Total Gate Charge (@ $V_{GS} = 10\text{V}$)	Q_g	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 50\text{V}, I_D = 20\text{A}$		69		nC
Total Gate Charge (@ $V_{GS} = 6.0\text{V}$)	Q_g			46		nC
Gate Source Charge	Q_{gs}			12.5		nC
Gate Drain Charge	Q_{gd}			18.9		nC
Turn-On DelayTime	$t_{D(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 50\text{V}$ $R_L = 2.5\Omega, R_{GEN} = 3\Omega$		21		ns
Turn-On Rise Time	t_r			35		ns
Turn-Off DelayTime	$t_{D(off)}$			49		ns
Turn-Off Fall Time	t_f			30		ns
Body Diode Reverse Recovery Time	t_{rr}		$I_F = 20\text{A}, di_F/dt = 100\text{A}/\mu\text{S}$		71	
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 20\text{A}, di_F/dt = 100\text{A}/\mu\text{S}$		127		nC

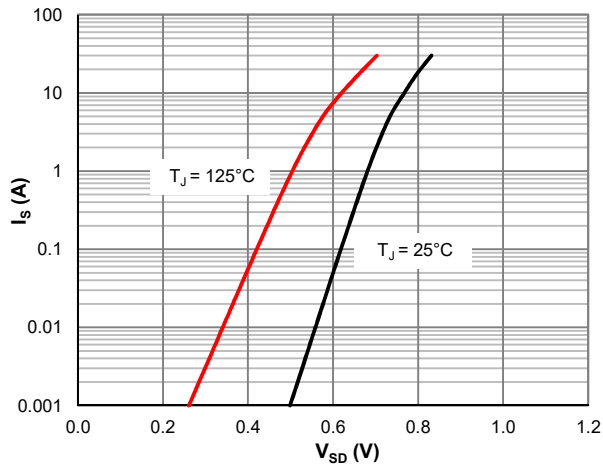
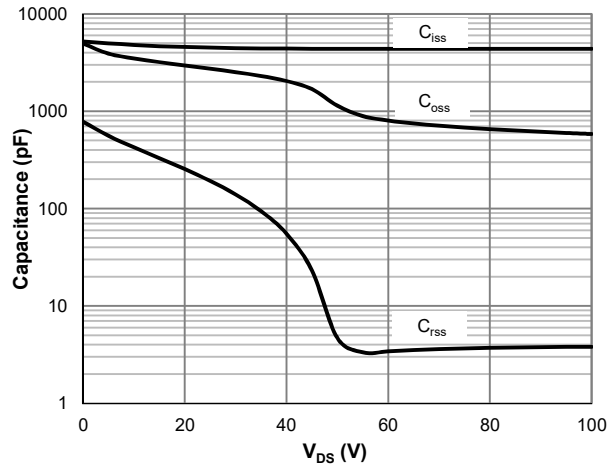
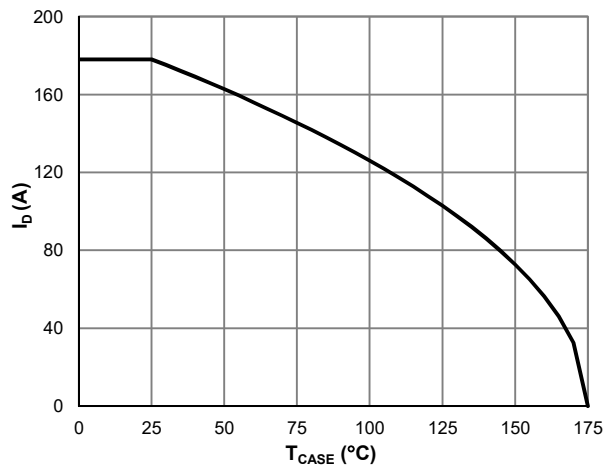
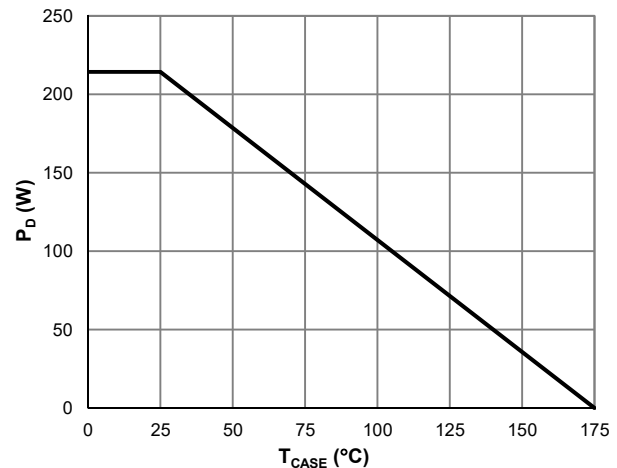
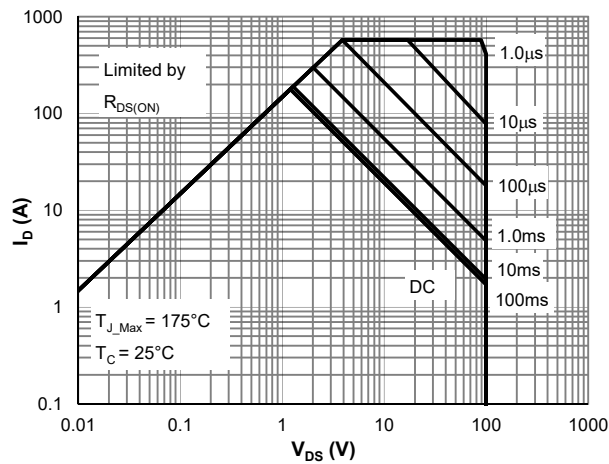
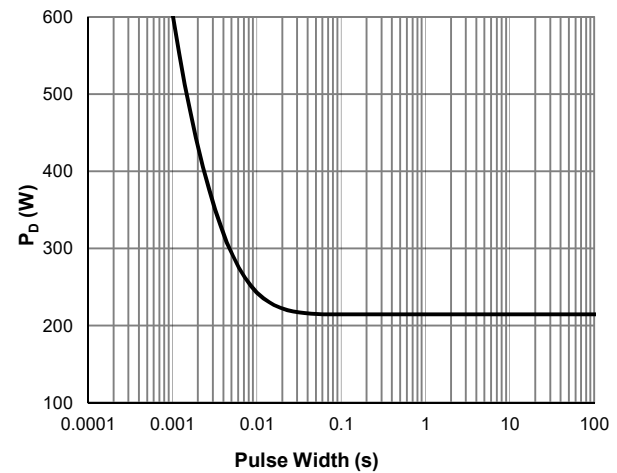
Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	60	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.70	0.91	$^\circ\text{C}/\text{W}$

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under $T_{J_Max} = 175^\circ\text{C}$.
3. E_{AS} of 481 mJ is based on starting $T_J = 25^\circ\text{C}$, $L = 1.0\text{mH}$, $I_{AS} = 31\text{A}$, $V_{GS} = 10\text{V}$, $V_{DD} = 50\text{V}$; 100% test at $L = 0.3\text{mH}$, $I_{AS} = 48\text{A}$, $T_{J_Max} = 175^\circ\text{C}$.
4. The power dissipation P_D is based on $T_{J_Max} = 175^\circ\text{C}$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Electrical & Thermal Characteristics

Figure 1: Saturation Characteristics

Figure 2: Transfer Characteristics

Figure 3: $R_{DS(ON)}$ vs. Drain Current

Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

Figure 5: $V_{GS(th)}$ vs. Junction Temperature

Figure 6: $V_{BR(DSS)}$ vs. Junction Temperature

Typical Electrical & Thermal Characteristics

Figure 7: Body-Diode Characteristics

Figure 8: Capacitance Characteristics

Figure 9: Current De-rating

Figure 10: Power De-rating

Figure 11: Maximum Safe Operating Area

Figure 12: Single Pulse Power Rating, Junction-to-Case

Typical Electrical & Thermal Characteristics

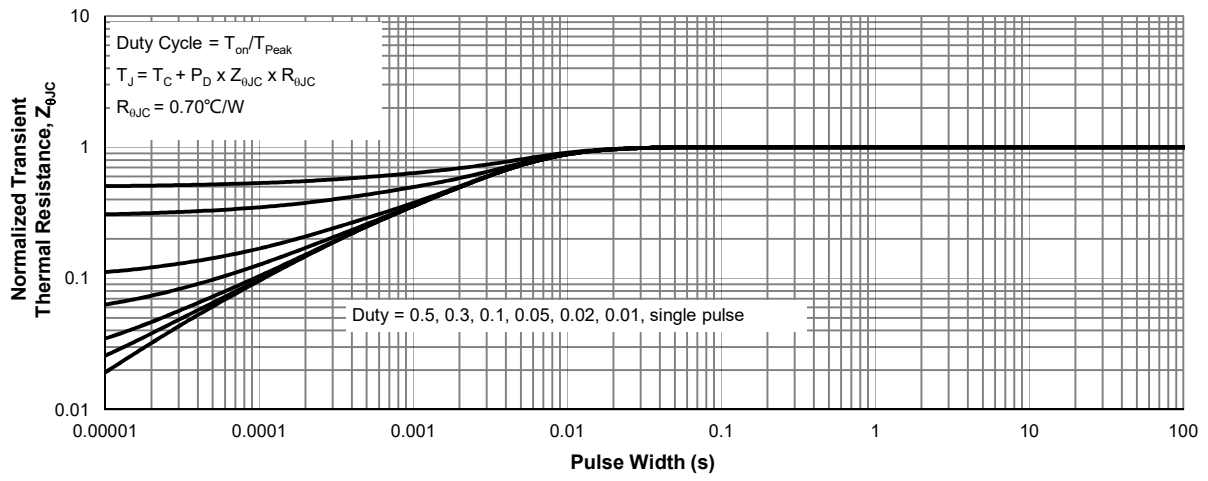
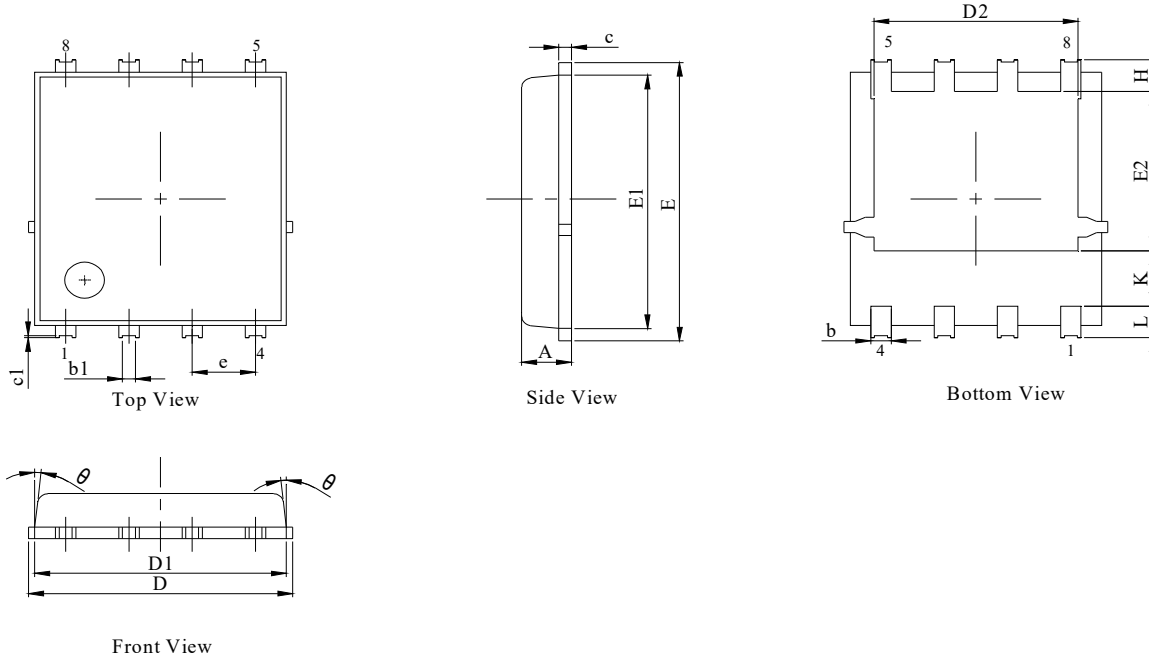
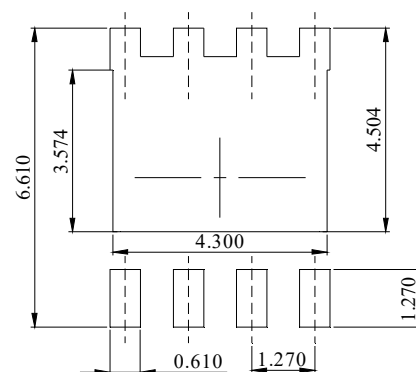


Figure 13: Normalized Maximum Transient Thermal Impedance

PDFN5x6-8L-W Package Information
Package Outline

NOTES:

1. Dimension and tolerance per ASME Y14.5M, 1994.
2. All dimensions in millimeter (angle in degree).
3. Dimensions D_1 and E_1 do not include mold flash protrusions or gate burrs.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
b	0.31	0.41	0.51
b_1	0.26 REF		
c	0.20	0.25	0.30
c_1	0.05 REF		
D	5.00	5.20	5.40
D_1	4.95	5.05	5.15
D_2	4.00	4.10	4.20
E	6.05	6.15	6.25
E_1	5.50	5.60	5.70
E_2	3.42	3.53	3.63
e	1.27BSC		
H	0.60	0.70	0.80
L	0.50	0.70	0.80
K	1.225 REF		
θ	-	-	10°

Recommended Soldering Footprint


DIMENSIONS: MILLIMETERS

Jiangsu JieJie Microelectronics Co., Ltd.

单击下面可查看定价，库存，交付和生命周期等信息

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